# Abstracts

## A New Low-Noise FET Structure

*G.A. Truitt, D.D. Heston and J.L. Klein. "A New Low-Noise FET Structure." 1990 Transactions on Microwave Theory and Techniques 38.12 (Dec. 1990 [T-MTT] (1990 Symposium Issue)): 1944-1948.*

A new monolithic FET topology has demonstrated improved minimum noise figure when compared with a conventional pi-gate FET. The new structure, referred to as the spider FET, has allowed noise figures to be achieved in monolithic LNA applications that are 0.3 dB lower using the standard 0.5 µm GaAs MESFET ion-implantation process.

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